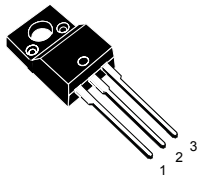
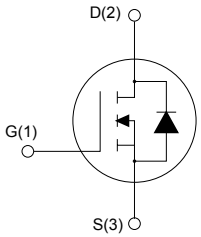
STF20N95DK5

Datasheet

N-channel 950 V, 275 mΩ typ., 18 A, MDmesh DK5 Power MOSFET in a TO-220FP package



TO-220FP



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Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STF20N95DK5	950 V	330 mΩ	18 A

- Fast-recovery body diode
- Best $R_{DS(on)}$ x area
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is part of the MDmesh DK5 fast-recovery diode series. The MDmesh DK5 combines very low recovery charge (Q_{rr}) and recovery time (t_{rr}) with an excellent improvement in $R_{DS(on)}$ * area and one of the most effective switching behaviors, ideal for half bridge and full bridge converters.

Product status link
STF20N95DK5

Product summary	
Order code	STF20N95DK5
Marking	20N95DK5
Package	TO-220FP
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	18	A
	Drain current (continuous) at T_C = 100 °C	11	
I_{DM}(1)	Drain current (pulsed)	72	A
P_{TOT}	Total power dissipation at T_C = 25 °C	28	W
dv/dt(2)	Peak diode recovery voltage slope	50	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 °C)	2.5	kV
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 18 A, di/dt ≤ 400 A/µs, V_{DS} (peak) ≤ $V_{(BR)DSS}$, V_{DD} = 760 V.*
3. *V_{DS} ≤ 760 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	4.4	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Maximum current during repetitive or single pulse avalanche	6	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	520	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	950			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 950 V			1	µA
		V_{GS} = 0 V, V_{DS} = 950 V, T_C = 125 °C(1)			100	µA
I_{GSS}	Gate source leakage current	V_{DS} = 0 V, V_{GS} = ±20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DD} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 9 A		275	330	mΩ

1. *Defined by design, not subject to production test.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	1600	-	pF
C_{oss}	Output capacitance		-	76	-	pF
C_{rss}	Reverse transfer capacitance		-	5	-	pF
$C_{o(tr)}$(1)	Equivalent capacitance time related	V_{GS} = 0 V, V_{DS} = 0 to 760 V	-	169	-	pF
$C_{o(er)}$(2)	Equivalent capacitance energy related		-	60	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	4	-	Ω
Q_g	Total gate charge	V_{DD} = 760 V, I_D = 18 A, V_{GS} = 0 to 10 V (see Figure 15. Test circuit for gate charge behavior)	-	50.7	-	nC
Q_{gs}	Gate source charge		-	7.8	-	nC
Q_{gd}	Gate drain charge		-	34.2	-	nC

1. *$C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.*
2. *$C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DS} = 475 V, I_D= 9 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	23	-	ns
t_r	Rise time		-	23	-	ns
$t_{d(off)}$	Turn-off delay time		-	74	-	ns
t_f	Fall time		-	25.4	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		18	A
I_{SDM}(1)	Source-drain current (pulsed)		-		72	A
V_{SD}(2)	Forward on voltage	I_{SD} = 18 A, V_{GS} = 0 V	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 9 A, di/dt = 100 A/µs,	-	150		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V	-	1		µC
I_{RRM}	Reverse recovery current	(see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	13.5		A
t_{rr}	Reverse recovery time	I_{SD} = 9 A, di/dt = 100 A/µs,	-	264		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V, T_J = 150 °C	-	2.9		µC
I_{RRM}	Reverse recovery current	(see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	22		A

1. *Pulse width limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

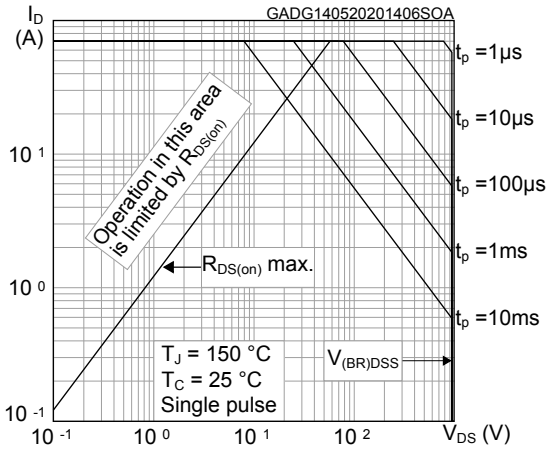


Figure 2. Maximum transient thermal impedance

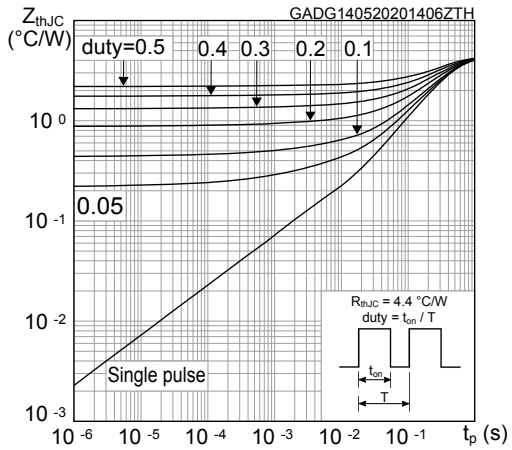


Figure 3. Output characteristics

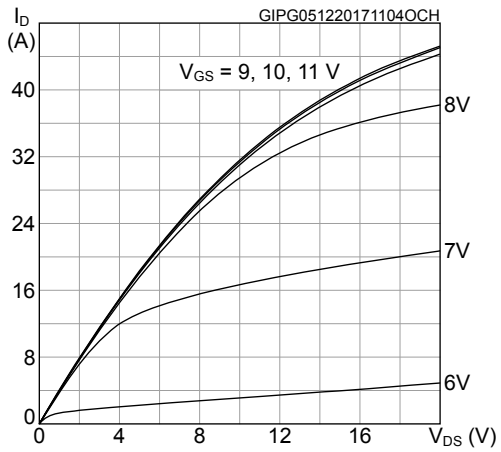


Figure 4. Transfer characteristics

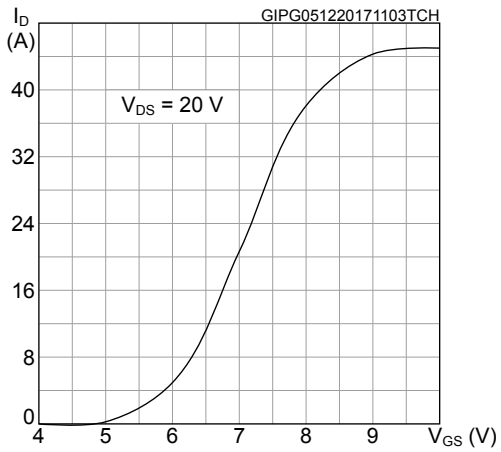


Figure 5. Gate charge vs gate-source voltage

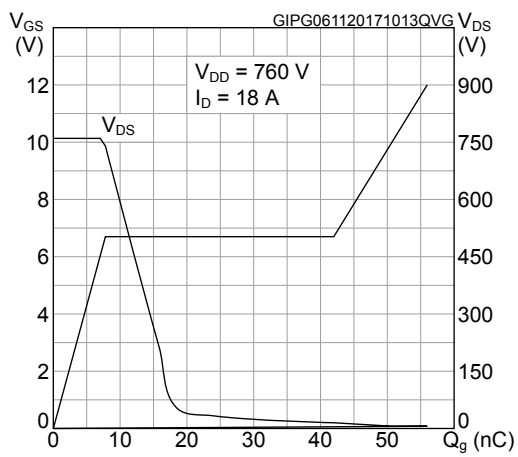


Figure 6. Static drain-source on-resistance

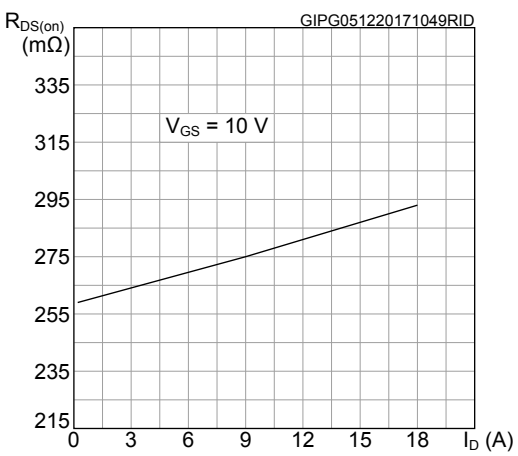


Figure 7. Capacitance variations

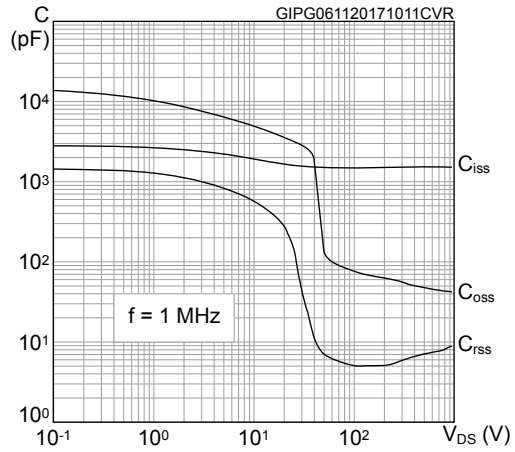


Figure 8. Output capacitance stored energy

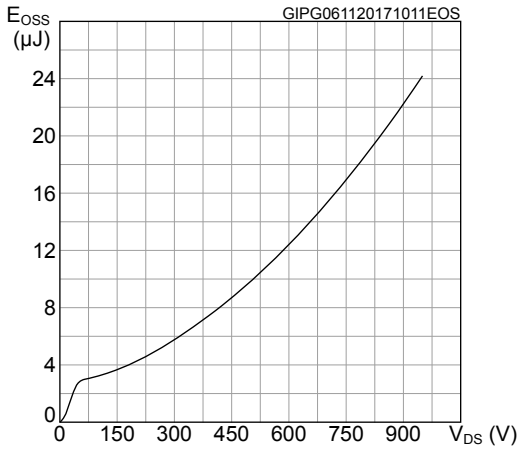


Figure 9. Normalized gate threshold voltage vs temperature

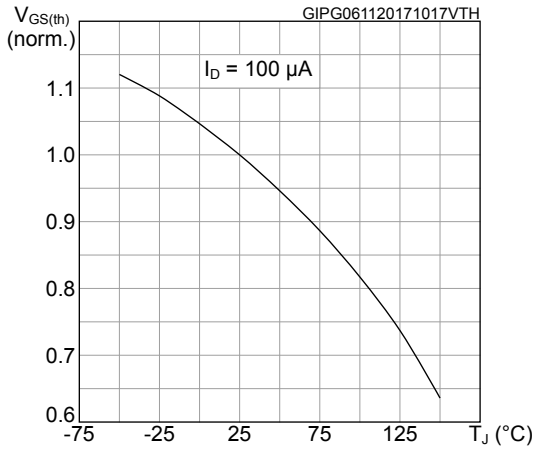


Figure 10. Normalized on-resistance vs temperature

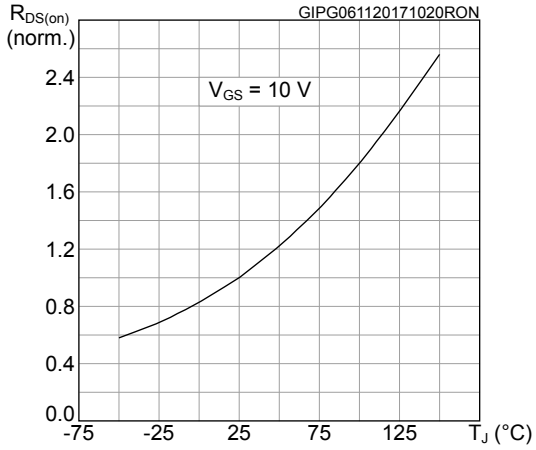


Figure 11. Normalized $V_{(BR)DSS}$ vs temperature

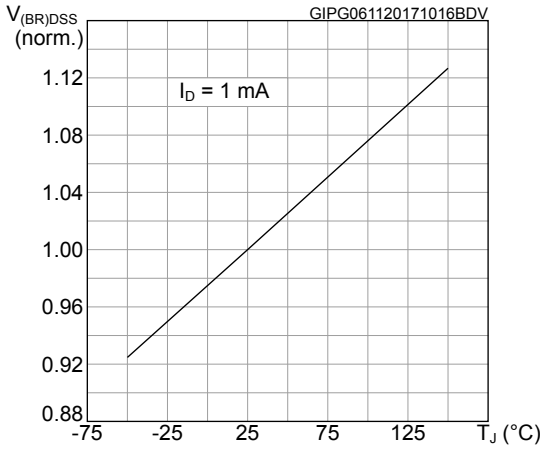


Figure 12. Source-drain diode forward characteristics

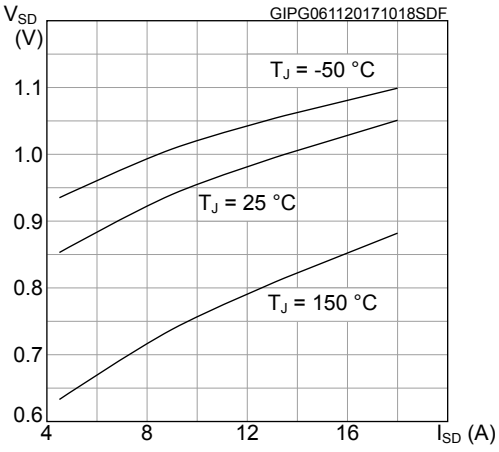
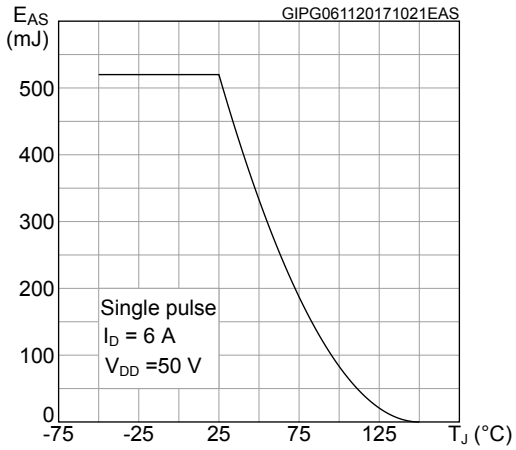


Figure 13. **Maximum avalanche energy vs starting T_J**



3 Test circuits

Figure 14. Test circuit for resistive load switching times

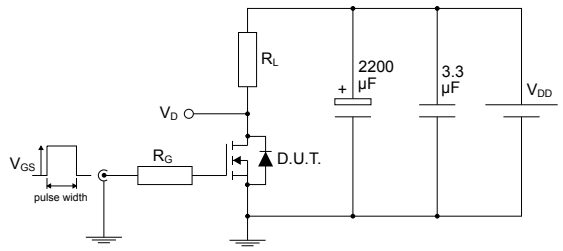


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Figure 15. Test circuit for gate charge behavior

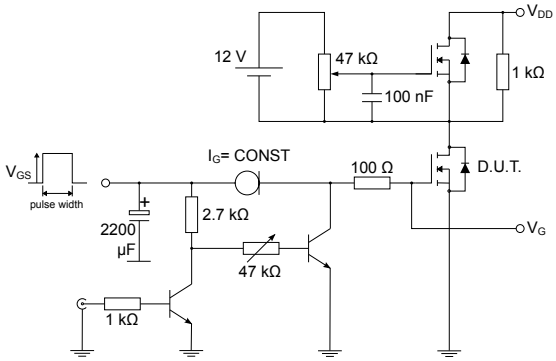

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Figure 16. Test circuit for inductive load switching and diode recovery times

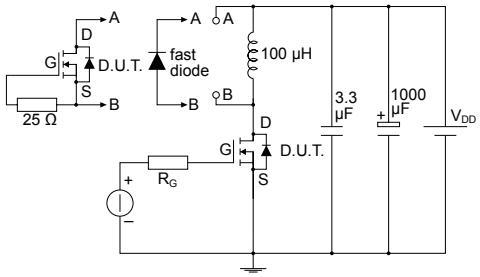

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Figure 17. Unclamped inductive load test circuit

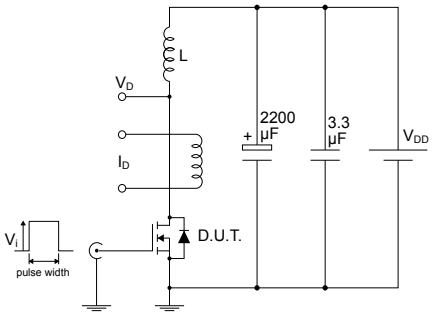

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Figure 18. Unclamped inductive waveform

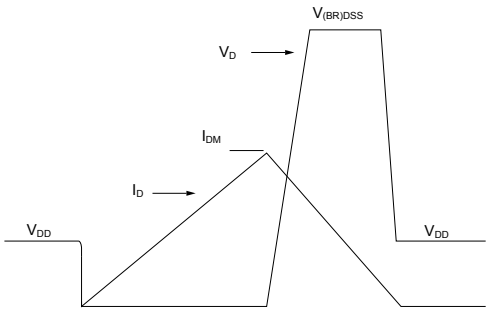

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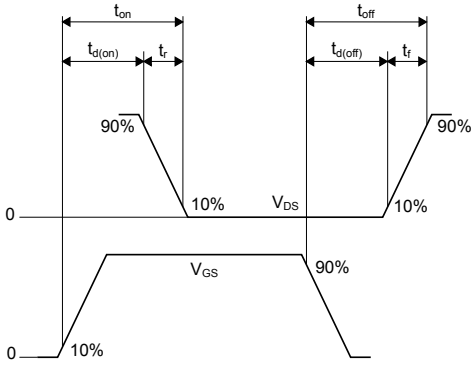
Figure 19. Switching time waveform



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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP package information

Figure 20. **TO-220FP package outline**

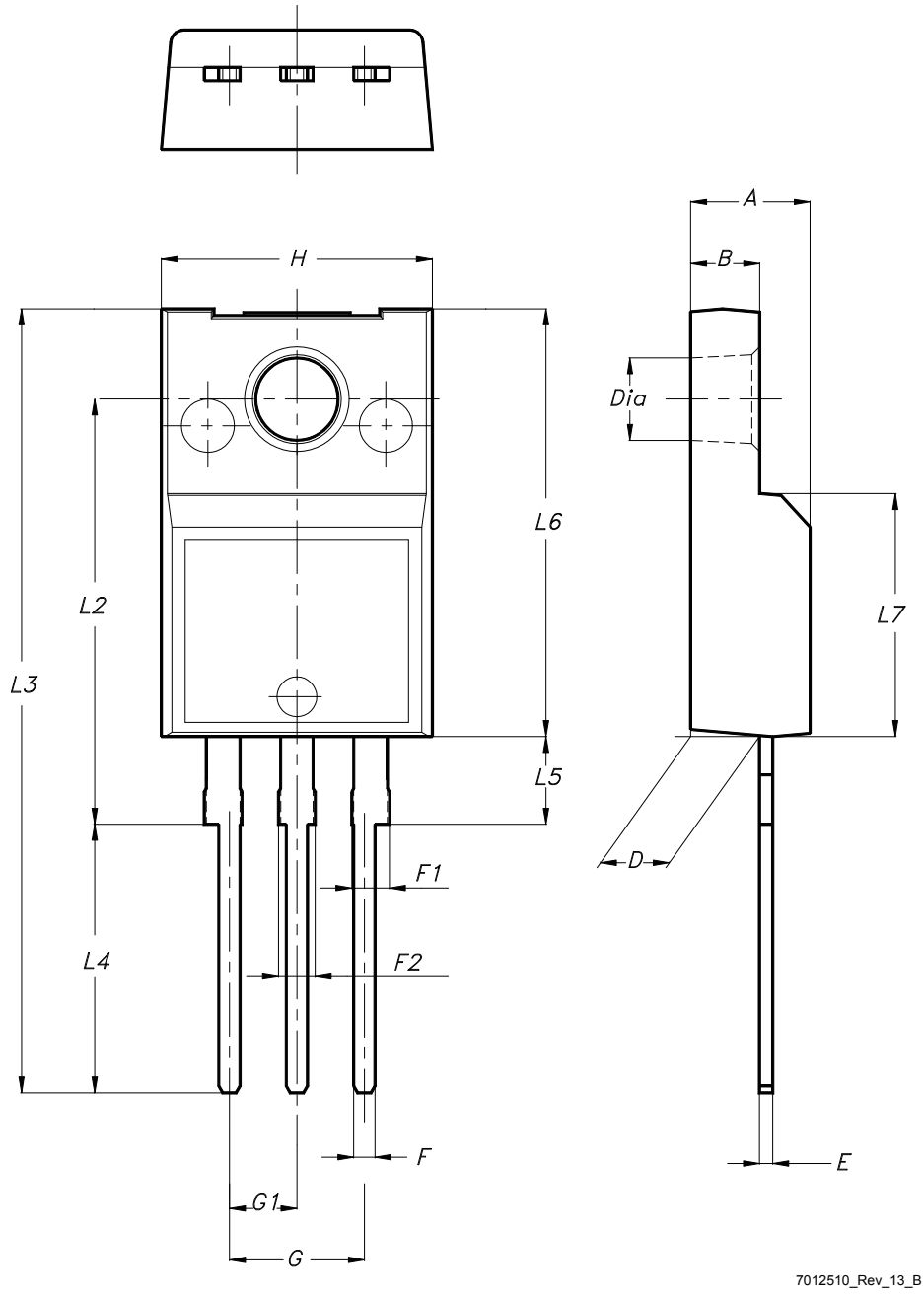

Table 8. **TO-220FP package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
15-May-2020	1	First release.
18-May-2020	2	Updated *Features* in cover page.
11-Aug-2021	3	Updated Table 1. Absolute maximum ratings. Updated Figure 3. Output characteristics, Figure 4. Transfer characteristics and Figure 6. Static drain-source on-resistance. Minor test changes.

Contents